

1.1 Scope.

This specification covers the detail requirements for a precision monolithic laser-trimmed BiFET amplifier.

1.2 Part Number.

The complete part number per Table 1 of this specification is as follows:

Device	Part Number
-1	AD548S(X)/883B

1.2.3 Case Outline.

See Appendix 1 of General Specification ADI-M-1000: package outline:

(X) Package Description
H H-08B 8-Pin Metal Package

1.3 Absolute Maximum Ratings. ($T_A = +25^\circ\text{C}$ unless otherwise noted)

Supply Voltage	$\pm 18 \text{ V}$
Internal Power Dissipation ¹	500 mW
Differential Input Voltage	$+V_S$ and $-V_S$
Output Short Circuit Duration	Indefinite
Storage Temperature Range	-65°C to $+150^\circ\text{C}$
Operating Temperature Range	-55°C to $+125^\circ\text{C}$
Lead Temperature (Soldering 60 sec)	$+300^\circ\text{C}$

NOTE

¹Maximum package power dissipation vs. ambient temperature.

Package Type	MAXIMUM AMBIENT	DERATE ABOVE MAXIMUM
	Temperature for Rating	Ambient Temperature
H-08B	80°C	3.3 mW/°C

1.5 Thermal Characteristics.

Thermal Resistance $\theta_{JC} = 65^\circ\text{C}/\text{W}$
 $\theta_{JA} = 150^\circ\text{C}/\text{W}$

AD548—SPECIFICATIONS

Table 1.

Test	Symbol	Device	Sub Group 1	Sub Group 2, 3	Test Conditions ¹	Units
Input Offset Voltage ²	V _{OS}	-1	2.0	3.0		±mV max
Input Offset Voltage Drift	TCV _{OS}	-1		20		±μV/°C max
Power Supply Rejection Ratio	PSRR	-1	80	76		dB min
Input Bias Current ³	I _B	-1	20		Either Input, V _{CM} = 0	±pA max
		-1	30		Either Input, V _{CM} = +10 V	±pA max
Input Offset Current ³	I _{OS}	-1	10		V _{CM} = 0	±pA max
Slew Rate	t _{SR}	-1	1.0		Unity Gain	V/μs min
Common-Mode Rejection Ratio	CMRR	-1	76	76	V _{CM} = ±10 V	dB min
			70	70	V _{CM} = ±11 V	
Open-Loop Gain	A _{OL}	-1	150/300	150/300	R _L = 5 kΩ/10 kΩ	V/mV min
Output Voltage Swing	V _{OUT}	-1	±12/±11	±12/±11	R _L = 10 kΩ/5 kΩ	±V min
Power Supply Current	I _Q	-1	0.2			mA max

NOTES

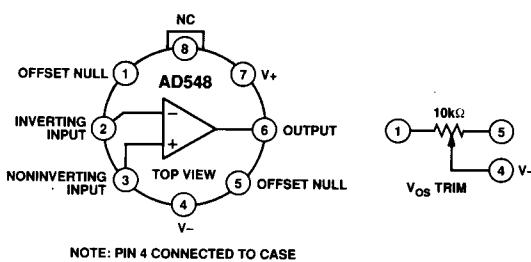
¹V_s = ±15 V unless otherwise noted.

²Input offset voltage specifications are guaranteed with after 5 minutes of operation at T_A = +25°C. Nulling will induce an additional ±3 μV/°C.

³Bias current specifications guaranteed after 5 minutes of operation at T_A = +25°C. For temperatures above +25°C, the current doubles every 10°C.

3.2.1 Functional Block Diagram and Terminal Assignments.

Top View



3.2.4 Microcircuit Technology Group.

This microcircuit is covered by technology group (85).

4.2.1 Life Test/Burn-In Circuit.

Steady state life test is per MIL-STD-883 Method 1005. Burn-in is per MIL-STD-883 Method 1015 test condition (B).

